

(43) Date of publication of application: 07.04.95

G11C 11/407
G11C 11/409

(71) Applicant: **SONY CORP**

(72) Inventor: **HASHIGUCHI AKIHIKO**

(54) SEMICONDUCTOR MEMORY DEVICE

(57) Abstract:

CONSTITUTION: When one word line is activated, a voltage VDBL for a dummy bit line DBL which is held at a prescribed potential and a preset reference voltage VBS are compared by a differential-type comparator CMP. When the voltage VDBL becomes the reference voltage VBS or higher, an activation signal SACT is generated, the signal is input to a driver for a sense amplifier S/A, and the sense amplifier is activated.

COPYRIGHT: (C)1995,JPO

